

Document Title**256Kx8 bit Super Low Power and Low Voltage Full CMOS Static RAM****Revision History**

<u>Revision No.</u>	<u>History</u>	<u>Draft Date</u>	<u>Remark</u>
0.0	Initial draft	October 2, 1996	Advance
0.1	Revise <ul style="list-style-type: none">- Remove sTSP1 from product- Rename high power product to low power. ISB1=10.0mA(Max)- Add super low power version with special handling ISB1=1.0mA(Max)- Remove 70ns and add 85ns part on KM68F2000 Family	December 1, 1996	Preliminary
1.0	Finalize	April 11, 1997	Final
2.0	Revise <ul style="list-style-type: none">- Change datasheet format- Remove reverse type package from product- Remove reserved speed bin(100ns)	March 5, 1998	Final

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256Kx8 bit Super Low Power and Low Voltage Full CMOS Static RAM

FEATURES

- Process Technology: Full CMOS
- Organization: 256Kx8
- Power Supply Voltage
 - K6F2008V2M Family: 3.0 ~ 3.6V
 - K6F2008S2M Family: 2.3 ~ 3.3V
 - K6F2008R2M Family: 1.8 ~ 2.7V
- Low Data Retention Voltage: 1.5V(Min)
- Three state output and TTL Compatible
- Package Type: 32-TSOP1-0820F

GENERAL DESCRIPTION

The K6F2008V2M, K6F2008S2M and K6F2008R2M families are fabricated by SAMSUNG's advanced Full CMOS process technology. The families support various operating temperature ranges and have various package types for user flexibility of system design. The families also supports low data retention voltage for battery back-up operation with low data retention current.

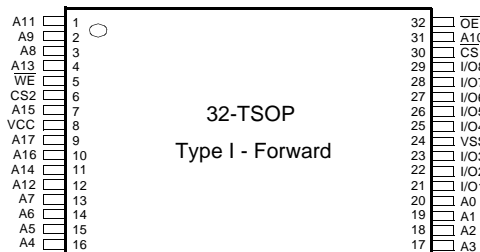
PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed(ns)	Power Dissipation		PKG Type
				Standby (I _{SB1} , Max)	Operating (I _{CC2} , Max)	
K6F2008V2M-C	Commercial(0~70°C)	3.0~3.6V	70 ¹⁾ /85@V _{CC} =3.3±0.3V	10μA ²⁾	60mA	32-TSOP1-F
K6F2008S2M-C		2.3~3.3V	85@V _{CC} =3.0±0.3V 120 ¹⁾ /150@V _{CC} =2.5±0.2V		55mA 30mA	
K6F2008R2M-C		1.8~2.7V	300 ¹⁾ @V _{CC} =2.0±0.2V		15mA	
K6F2008V2M-I	Industrial(-40~85°C)	3.0~3.6V	70 ¹⁾ /85@V _{CC} =3.3±0.3V		60mA	
K6F2008S2M-I		2.3~3.3V	85@V _{CC} =3.0±0.3V 120 ¹⁾ /150@V _{CC} =2.5±0.2V		55mA 30mA	
K6F2008R2M-I		1.8~2.7V	300 ¹⁾ @V _{CC} =2.0±0.2V		15mA	

1. The parameter is measured with 30pF test load.

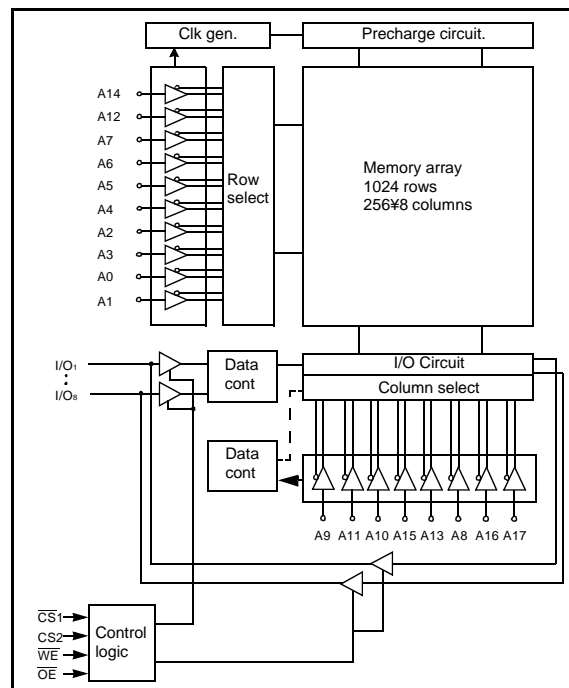
2. 2μA for super low power version with special handling.

PIN DESCRIPTION



Name	Function	Name	Function
CS ₁ , CS ₂	Chip Select Input	I/O ₁ ~I/O ₈	Data Inputs/Outputs
OE	Output Enable	Vcc	Power
WE	Write Enable Input	Vss	Ground
A ₀ ~A ₁₇	Address Inputs	N.C.	No Connection

FUNCTIONAL BLOCK DIAGRAM



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PRODUCT LIST

Commercial Temperature Products(0~70°C)		Industrial Temperature Products(-40~85°C)	
Part Name	Function	Part Name	Function
K6F2008V2M-TC70 K6F2008V2M-TC85	32-TSOP F, 70ns, 3.3V, LL 32-TSOP F, 85ns, 3.3V, LL	K6F2008V2M-TI70 K6F2008V2M-TI85	32-TSOP F, 70ns, 3.3V, LL 32-TSOP F, 85ns, 3.3V, LL
K6F2008S2M-TC12 K6F2008S2M-TC15	32-TSOP F, 120/85ns, 2.5/3.0V, LL 32-TSOP F, 150/85ns, 2.5/3.0V, LL	K6F2008S2M-TI12 K6F2008S2M-TI15	32-TSOP F, 120/85ns, 2.5/3.0V, LL 32-TSOP F, 150/85ns, 2.5/3.0V, LL
K6F2008R2M-TC30	32-TSOP F, 300ns, 2.0/2.5V, LL	K6F2008R2M-TI30	32-TSOP F, 300ns, 2.0/2.5V, LL

FUNCTIONAL DESCRIPTION

CS ₁	CS ₂	OE	WE	I/O	Mode	Power
H	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
X ¹⁾	L	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
L	H	H	H	High-Z	Output Disable	Active
L	H	L	H	Dout	Read	Active
L	H	X ¹⁾	L	Din	Write	Active

1. X means don't care (Must be high or low states)

ABSOLUTE MAXIMUM RATINGS¹⁾

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to V _{SS}	V _{IN} , V _{OU}	-0.2 to 3.6V ²⁾	V	-
Voltage on V _{CC} supply relative to V _{SS}	V _{CC}	-0.2 to 4.0V ³⁾	V	-
Power Dissipation	P _D	1.0	W	-
Storage temperature	T _{STG}	-55 to 150	°C	-
Operating Temperature	T _A	0 to 70	°C	K6F2008V2M-C, K6F2008S2M-C, K6F2008R2M-C
		-40 to 85	°C	K6F2008V2M-I, K6F2008S2M-I, K6F2008R2M-I
Soldering temperature and time	T _{SOLDER}	260°C, 5sec (Lead Only)	-	-

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. V_{IN}/V_{OUT}= -0.2 to 3.9V for K6F2008V2M Family.

3. Maximum V_{CC}= -0.2 to 4.6V for K6F2008V2M Family.

RECOMMENDED DC OPERATING CONDITIONS¹⁾

Item	Symbol	Product	Min	Typ ²⁾	Max	Unit
Supply voltage	V _{CC}	K6F2008V2M Family K6F2008S2M Family K6F2008R2M Family	3.0 2.3 1.8	3.3 2.5/3.0 2.0/2.5	3.6 3.3 2.7	V
Ground	V _{SS}	All Family	0	0	0	V
Input high voltage	V _{IH}	K6F2008V2M Family K6F2008S2M Family K6F2008R2M Family	V _{CC} =3.3±0.3V V _{CC} =3.0±0.3V V _{CC} =2.5±0.2V V _{CC} =2.5±0.2V V _{CC} =2.0±0.2V	2.2 2.2 2.0 2.0 1.6	-	V _{CC} +0.2 ²⁾ V
Input low voltage	V _{IL}	All Family	-0.2 ³⁾	-	0.4	V

Note

1. Commercial Product : T_A=0 to 70°C, unless otherwise specifiedIndustrial Product : T_A=-40 to 85°C, unless otherwise specified2. Overshoot : V_{CC} + 1.0V in case of pulse width≤20ns

3. Undershoot : -1.0V in case of pulse width≤20ns

4. Overshoot and undershoot are sampled, not 100% tested.

CAPACITANCE¹⁾ (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C _{IN}	V _{IN} =0V	-	8	pF
Input/Output capacitance	C _{IO}	V _{IO} =0V	-	10	pF

1. Capacitance is sampled, not 100% tested

DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions	Min	Typ	Max	Unit
Input leakage current	I _{LI}	V _{IN} =V _{SS} to V _{CC}	-1	-	1	mA
Output leakage current	I _{LO}	$\overline{CS}_1=V_{IH}$ or $CS_2=V_{IL}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$, V _{IO} =V _{SS} to V _{CC}	-1	-	1	mA
Operating power supply current	I _{CC}	I _{IO} =0mA, $\overline{CS}_1=V_{IL}$, $CS_2=V_{IH}$, V _{IN} =V _{IL} or V _{IH} , Read	-	-	10	mA
Average operating current	I _{CC1}	Cycle time=1μs, 100% duty, I _{IO} =0mA, $\overline{CS}_1\leq 0.2V$, $CS_2\geq V_{CC}-0.2V$, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	Read	-	-	10
			Write	-	-	15
	I _{CC2}	Cycle time=Min, 100% duty, I _{IO} =0mA, $\overline{CS}_1=V_{IL}$, $CS_2=V_{IH}$, V _{IN} =V _{IL} or V _{IH}	V _{CC} =3.3V@70ns	-	-	55 ¹⁾
			V _{CC} =2.7V@120ns	-	-	30
			V _{CC} =2.2V@300ns	-	-	15
Output low voltage	V _{OL}	I _{OL}	2.1mA at V _{CC} =3.0/3.3V	-	-	0.4
			0.5mA at V _{CC} =2.5V	-	-	0.4
			0.33mA at V _{CC} =2.0V	-	-	0.4
Output high voltage	V _{OH}	I _{OH}	-1.0mA at V _{CC} =3.0/3.3V	2.4	-	-
			-0.5mA at V _{CC} =2.5V	2.0	-	-
			-0.44mA at V _{CC} =2.0V	1.6	-	-
Standby Current(TTL)	I _{SB}	$\overline{CS}_1=V_{IH}$ or $CS_2=V_{IL}$, Other inputs=V _{IL} or V _{IH}	-	-	0.3	mA
Standby Current(CMOS)	I _{SB1}	$\overline{CS}_1\geq V_{CC}-0.2V$, $CS_2\geq V_{CC}-0.2V$ or $CS_2\leq 0.2V$, Other inputs=0~V _{CC}	-	-	10 ²⁾	μA

1. The value is measured at V_{CC}=3.0±0.3V- I_{CC2}=60mA with 70ns at V_{CC}=3.3±0.3V, but this value is not 100% tested but obtained statistically.

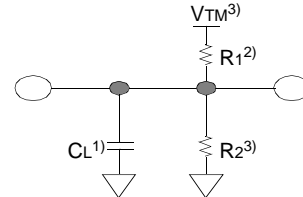
2. Super low power product = 2μA with special handling.

AC OPERATING CONDITIONS

TEST CONDITIONS (Test Load and Test Input/Output Reference)

Input pulse level: 0.4 to 2.2V for $V_{CC}=3.3V$, 3.0V, 2.5V0.4 to 1.8V for $V_{CC}=2.0V$

Input rising and falling time: 5ns

Input and output reference voltage: 1.5V for $V_{CC}=3.3V$, 3.0V1.1V for $V_{CC}=2.5V$ 0.9V for $V_{CC}=2.0V$ Output load (See right): $C_L=100pF+1TTL$ $C_L=30pF+1TTL$ 

1. Including scope and jig capacitance

2. $R_1=3070\Omega$, $R_2=3150\Omega$ 3. $V_{TM}=2.8V$ for $V_{CC}=3.0/3.3V$ $=2.3V$ for $V_{CC}=2.5V$ $=1.8V$ for $V_{CC}=2.0V$

AC CHARACTERISTICS

(Commercial product: $T_A=0$ to $70^\circ C$, Industrial product: $T_A=-40$ to $85^\circ C$)
 K6F2008V2M Family: $V_{CC}=3.0\sim 3.6V$, K6F2008S2M Family: $V_{CC}=2.3\sim 3.3V$,
 K6F2008R2M Family: $V_{CC}=1.8\sim 2.7V$)

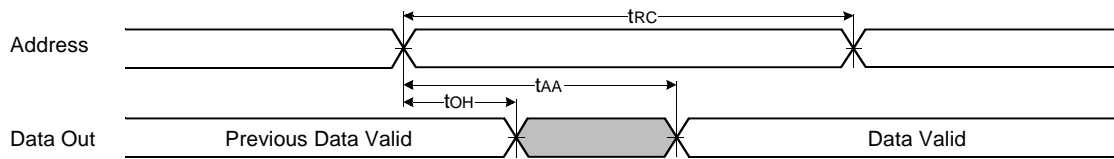
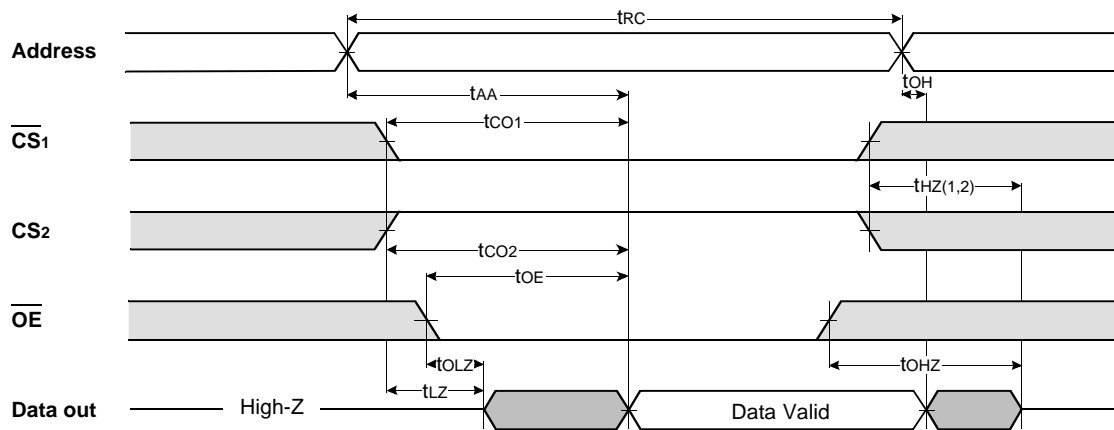
Parameter List		Symbol	Speed Bins										Units
			70ns		85ns		120ns		150ns		300ns		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Read	Read cycle time	t _{RC}	70	-	85	-	120	-	150	-	300	-	ns
	Address access time	t _{AA}	-	70	-	85	-	120	-	150	-	300	ns
	Chip select to output	t _{CO1} , t _{CO2}	-	70	-	85	-	120	-	150	-	300	ns
	Output enable to valid output	t _{OE}	-	35	-	45	-	60	-	75	-	150	ns
	Chip select to low-Z output	t _{LZ1} , t _{LZ2}	10	-	10	-	10	-	20	-	50	-	ns
	Output enable to low-Z output	t _{OLZ}	5	-	5	-	5	-	10	-	30	-	ns
	Chip disable to high-Z output	t _{HZ1} , t _{HZ2}	0	25	0	25	0	35	0	40	0	60	ns
	Output disable to high-Z output	t _{OHZ}	0	25	0	25	0	35	0	40	0	60	ns
	Output hold from address change	t _{OH}	10	-	15	-	15	-	15	-	30	-	ns
Write	Write cycle time	t _{WC}	70	-	85	-	120	-	150	-	300	-	ns
	Chip select to end of write	t _{CW}	65	-	70	-	100	-	120	-	300	-	ns
	Address set-up time	t _{AS}	0	-	0	-	0	-	0	-	0	-	ns
	Address valid to end of write	t _{AW}	65	-	70	-	100	-	120	-	300	-	ns
	Write pulse width	t _{WP}	55	-	60	-	80	-	100	-	200	-	ns
	Write recovery time	t _{WR}	0	-	0	-	0	-	0	-	0	-	ns
	Write to output high-Z	t _{WHZ}	0	25	0	25	0	35	0	40	0	60	ns
	Data to write time overlap	t _{DW}	30	-	35	-	50	-	60	-	120	-	ns
	Data hold from write time	t _{DH}	0	-	0	-	0	-	0	-	0	-	ns
	End write to output low-Z	t _{OW}	5	-	5	-	5	-	5	-	20	-	ns

DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition	Min	Typ	Max	Unit
V_{CC} for data retention	V_{DR}	$\overline{CS}_1 \geq V_{CC}-0.2V^{(1)}$	1.5	-	3.6	V
Data retention current	I_{DR}	$V_{CC}=3.0V$, $\overline{CS}_1 \geq V_{CC}-0.2V^{(1)}$	-	-	$10^{(2)}$	μA
Data retention set-up time	t _{SDR}	See data retention waveform	0	-	-	ns
Recovery time	t _{RDR}		t _{RC}	-	-	

1. $\overline{CS}_1 \geq V_{CC}-0.2V$, $\overline{CS}_2 \geq V_{CC}-0.2V$ (\overline{CS}_1 controlled) or $\overline{CS}_2 \leq 0.2V$ (\overline{CS}_2 controlled)2. Super low power product = $2\mu A$ with special handling.

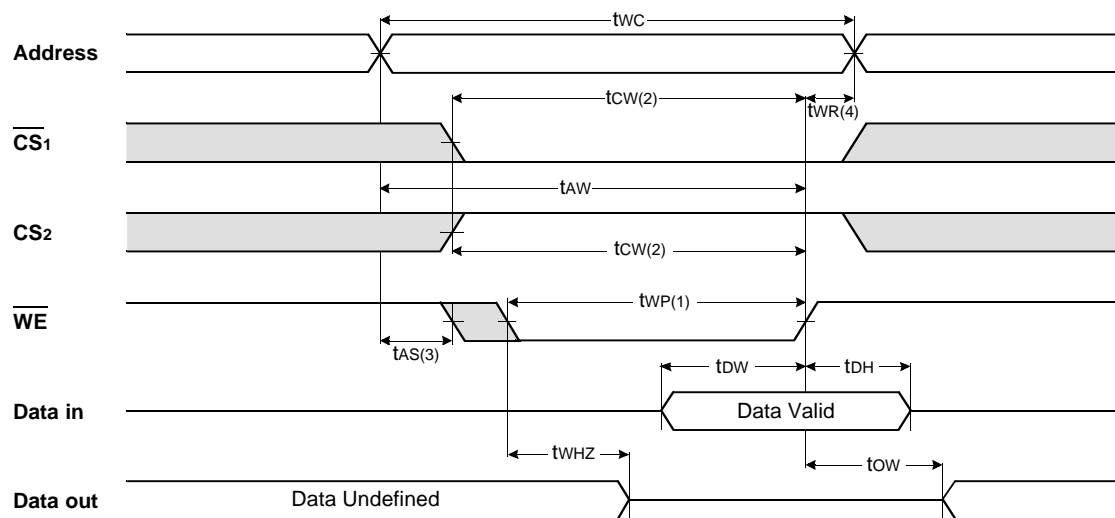
TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS1}=\overline{OE}=V_{IL}$, $\overline{WE}=V_{IH}$)TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)

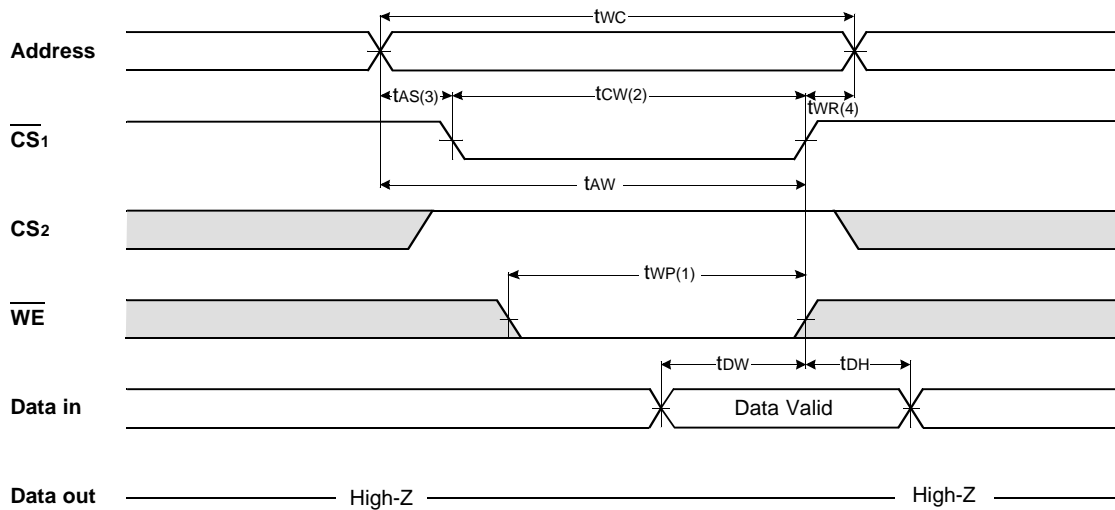
NOTES (READ CYCLE)

1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device interconnection.

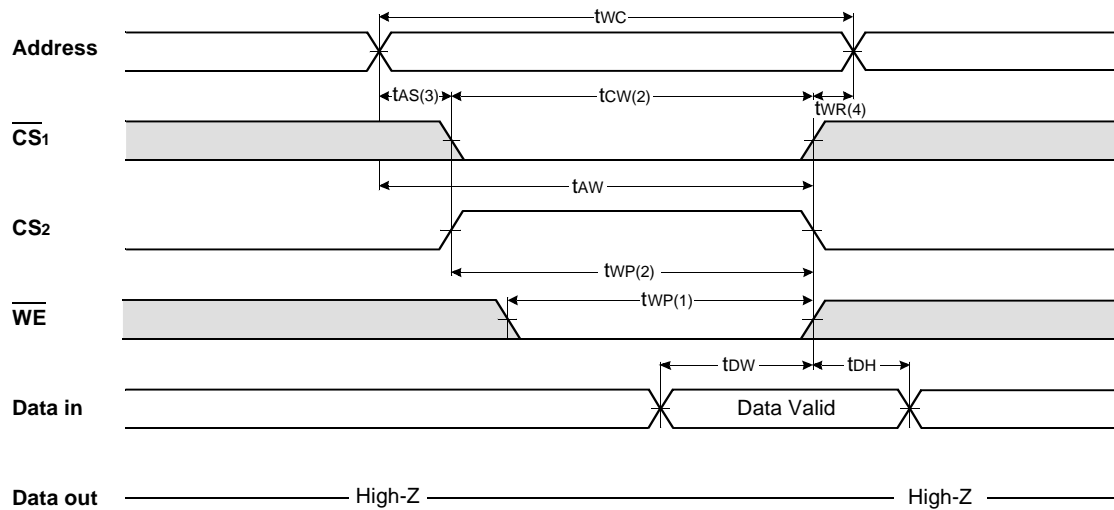
TIMING WAVEFORM OF WRITE CYCLE(1) ($\overline{\text{WE}}$ Controlled)



TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{\text{CS1}}$ Controlled)



TIMING WAVEFORM OF WRITE CYCLE(3) ($\overline{CS_1}$ Controlled)

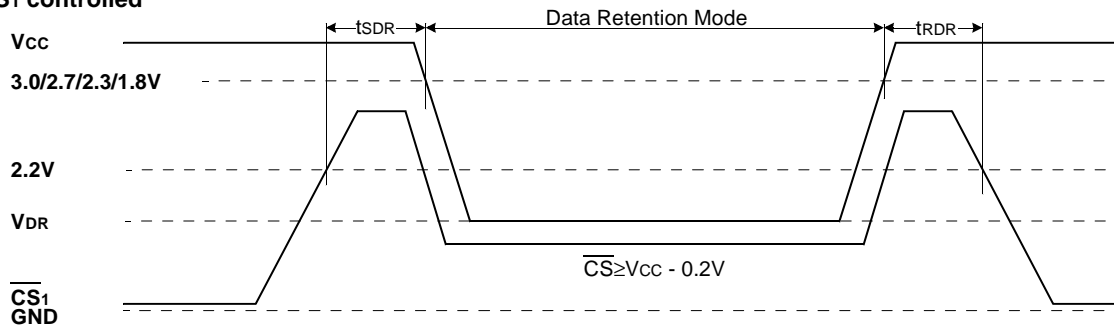


NOTES (WRITE CYCLE)

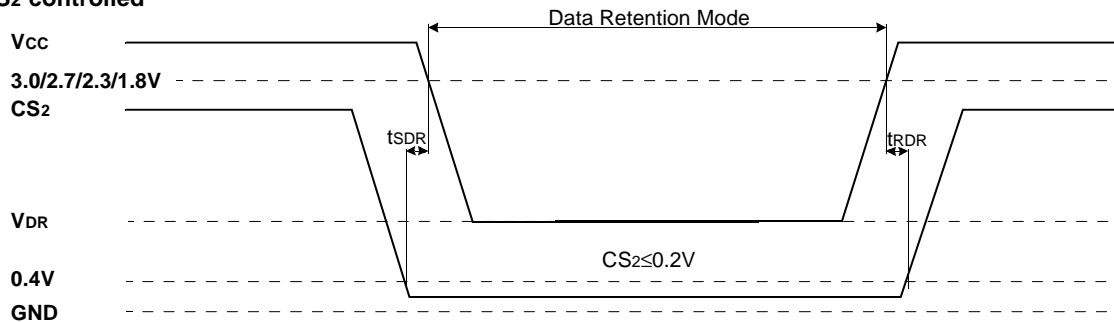
1. A write occurs during the overlap of a low $\overline{CS_1}$, a high $\overline{CS_2}$ and a low \overline{WE} . A write begins at the latest transition among $\overline{CS_1}$ goes low, $\overline{CS_2}$ going high and \overline{WE} going low : A write ends at the earliest transition among $\overline{CS_1}$ going high, $\overline{CS_2}$ going low and \overline{WE} going high, t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the $\overline{CS_1}$ going low or $\overline{CS_2}$ going high to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. $t_{WR(1)}$ applied in case a write ends as $\overline{CS_1}$ or \overline{WE} going high $t_{WR(2)}$ applied in case a write ends as $\overline{CS_2}$ going low.

DATA RETENTION WAVE FORM

$\overline{CS_1}$ controlled



$\overline{CS_2}$ controlled



PACKAGE DIMENSIONS

Units: millimeters(inches)

32 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0820F)

